
High Precision, Low Noise, Current Sensor IC With REF or OCD

1 Features

- Industry-leading noise performance with greatly improved bandwidth for fast control loops or where high-speed current monitored: 400 KHZ bandwidth and 1.2us typical response time.
- High accuracy performance: sensitivity error < 1.5% in full temperature range; offset voltage < 20mV in full temperature range.
- 2 versions respectively support 3.3V & 5V applications and Selectable analog ratiometric output
- Various adjustable error detection modes: OVP OTP OCD
- Non-ratiometric output with fixed VREF bidirectional operation: input or output.
- AEC-Q100-Grade 0 Automotive Qualification
- 24 Bit customer ID
- Diagnostic capability
- sensor range from 0.4mV/GS~4 mV/GS

2 Applications

- High Voltage Traction Motor Inverter
- Smart Battery Junction Boxes
- Smart Fuse Overcurrent Detection
- DCDC Converter

3 Description

The SC4665 is a monolithic programmable Hall sensor IC featuring the planar Hall technology, which is sensitive to the flux density applied orthogonally to the IC surface. The sensor provides an output signal proportional to the applied magnetic flux density and is preferably suited for current measurement.

The transfer characteristic of the SC4665 is factory trimmed over temperature, and is programmable (offset, sensitivity, filtering, internal over-current threshold) during end-of-line customer calibration. With up to 400 kHz bandwidth and fast response time, it is particularly adapted for high speed applications such as inverters and converters where fast response time due to fast switching is required. The output clamping levels and on-chip filtering are also programmable as a function of application needs.

The sensor is designed for automotive and hostile industrial applications and operates with typically 3.3V or 5 V supply voltage in the ambient temperature range from -40 up to 150 °C. The 4665 is available in a selectable SIP4 package with either REF or OCD functionality

目录

1 Features	- 1 -
2 Applications	- 1 -
3 Description	- 1 -
4 Revision History	- 3 -
5 Device Information	- 3 -
6 Pin configuration and Functions	- 4 -
7 Specification	- 5 -
7.1 Absolute Maximum Ratings	- 5 -
7.2 ESD Protection	- 5 -
7.3 Electrical /Magnetic Parameter	- 6 -
8 Detail Description	- 10 -
8.1 Overview	- 10 -
8.2 Functional Block Diagram	- 10 -
8.3 Feature Description	- 10 -
8.4 EEPROM Programming Information	- 13 -
9 Characteristic Definitions	- 21 -
10 Typical Application Diagram	- 28 -
11 Transfer Function	- 29 -
12 Package Designator	- 30 -
12.1 Package(SIP4-VB)	- 30 -
12.2 Package(SIP3-VB)	- 32 -

4 Revision History

Version	Date	Change	Name
Rev 1.0			

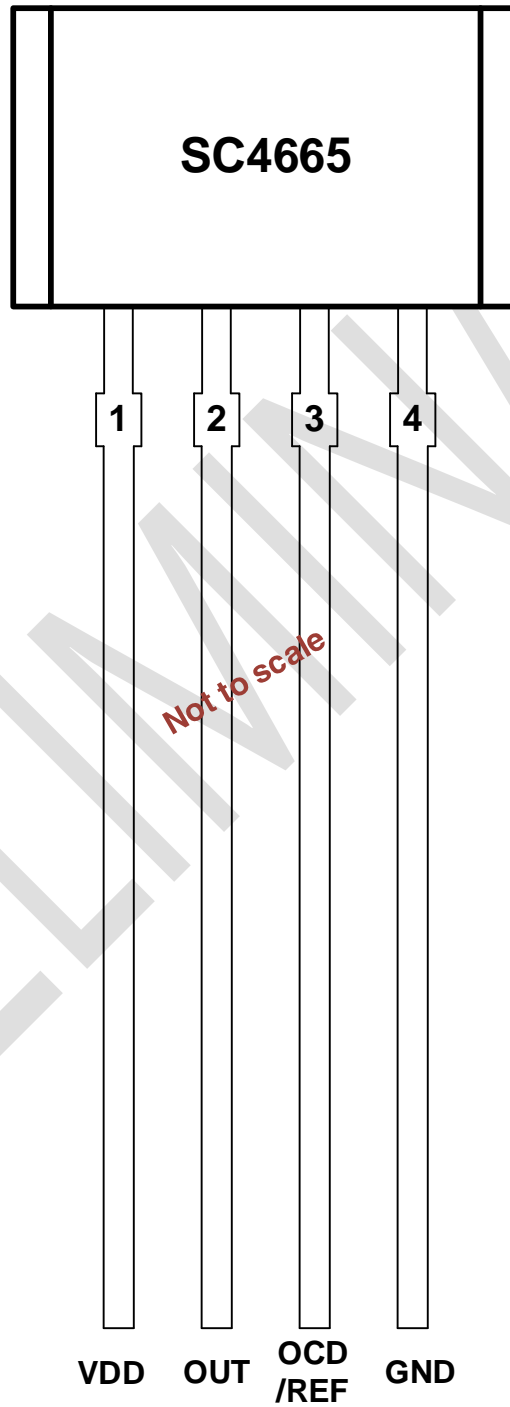
5 Device Information

Part Number	Temperature	Package	Packing Form	function	Marking
SC4665	L	SIP4-VB	Bulk	OCD	4665
SC4665	L	SIP4-VB	Bulk	Vref	4665

6 Pin configuration and Functions

6.1 SIP4-VB

4-Terminal SIP
VB Package
(Top View)



Terminal		Type	Description
Name	Number		
VCC	1	PWR	power supply.
OUT	2	Output	Output voltage
OCD	3	Output	Open-drain output. The open drain requires a pull-up resistor
REF	3	Output	Analog output voltage
GND	4	Ground	Ground terminal

7 Specification

7.1 Absolute Maximum Ratings

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Characteristic	Symbol	Notes	Min.	Max.	Unit
Positive Supply Voltage(DC)	VDD_abs1	VDD=0 to 10V	-	6	V
Negative Supply Voltage	VDDR_abs	VDD=0 to -1.0V	-	-0.2	V
Positive VOUT Voltage	VOUT_abs	VOUT=0 to 10V	-	VDD+0.2	V
Negative VOUT Voltage	VOUTr_abs	VDD=0 to -1.0V	-	-0.3	V
VOUT Short Current to GND	IShort_GND	VOUT=GND	-	20	mA
VOUT Short Current to VDD	IShort_VDD	VOUT=VDD	-	25	mA
Output Sinking Current	Iout_sink	VOUT Diff <100mV	-	13	mA
Output Source Current	Iout_source	VOUT Diff <100mV	-	13	mA
Operating Temperature Range	TA		-40	150	°C
Storage Temperature Range	TSTG		-55	165	°C
Maximum Junction Temperature	TJ(max)		-	165	°C
HBM ESD Rating	ESDHBM		4	8	kV

7.2 ESD Protection

Human Body Model (HBM) tests according to: standard EIA/JESD22-A114-B HBM

Parameter	Symbol	Min.	Max.	Units
HBM ESD stress voltage	VESD	-4000	8000	V

7.3 Electrical /Magnetic Parameter

valid through the full operate temperature range, VDD=5V, CBY=0.1uF, unless otherwise specified						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Electrical Specifications						
Supply Voltage	VDD	5V device only	4.5	5	5.5	V
		3.3V device only	3.15	3.3	3.6	
Supply Current	IDD	No load on VOUT or VREF; VCC = 5 V	-	9	-	mA
		No load on VOUT or VREF; VCC = 3.3 V				
Supply Bypass Capacitor	CBYPASS	VCC to GND recommended	0.1	-	-	μF
Reference Resistive Load	RVREF	VREF to GND,VREF to VCC	1			KΩ
Reference Capacitive Load	CVREF	VREF to GND			6	nF
Power-On Delay	Tpo	VDD=0 to 5,Time from VCC=90% to VOUT=90%	-	77	-	uS
Power-On Reset Voltage	VPOR(H)	VDD=0 to 5.5	-	2.9	-	V
	VPOR(L)	VDD=5.5 to 0	-	2.6	-	V
Under-voltage Protection	UVLOH	VDD=0 to 5.5V	-	4.1	4.3	V
	UVLOL	VDD=5 to 0V		3.25		V
Overvoltage Protection (OVP) Threshold	VOVPH	VDD rising	-	6.4	-	V
	VOVPH	VDD rising		5.9		V
OVP Delay Time	tdOVD(E)	Time from VCC rising \geq VOV(EN) until OVP asserts		54		uS
	tdOVD(D)	Time from VCC falling \leq VOV(DIS) until OVP clears		7.6		uS
Response Time	TRES	CLoad, Sen,EENoise, EEBW ,All temp	-	2	-	uS
Rise Time	Tr	CLoad, Sen,EENoise, EEBW ,All temp	-	-	3	uS
VOUT Load Current	IOUT	VDD=4.5--5.5, VOUT=0.5--4.5, Iload=-10--10mA	-	9	-	mA
VOUT Output Resistance	ROUT	VOUT=VQ, ILOAD=5mA	-	11	-	Ω

Output Capacitive Load	COUT	EE_CL = 0	1	-	4.7	nF
Output Capacitive Load	COUT	EE_CL = 1	4.7	-	10	nF
Output Leakage Current	ILEAK	High Impedance Mode	-	6	20	uA
Output Load Resistance	RLoadL	VOUT to GND, RL=10k to 1k, B=+BMAX	1	-	-	kΩ
	RLoadH	VOUT to VCC, RL=10k to 1k, B=-BMAX	1	-	-	kΩ
Clamped Output Voltage(EE_Clamp level=0)	Clamp_lo	B=-BMAX, RL=5k to VDD EE_CL=enable	-	5	-	%VDD
	Clamp_hi	B=+BMAX, RL=5k to GND EE_CL=enable	-	95	-	%VDD
Clamped Output Voltage(EE_Clamp level=1)	Clamp_lo	B=-BMAX, RL=5k to VDD EE_CL=enable	-	7.5	-	%VDD
	Clamp_hi	B=+BMAX, RL=5k to GND EE_CL=enable	-	92.5	-	%VDD
Clamped Output Accuracy	CLACC	B=+BMAX, RL=5k to GND EECL=enable	-	-	1	%VDD
Saturation Voltage	VSAT(H)	B=-BMAX, RL=5k to VDD EE_CL=enable		0.5		%VDD
	VSAT(L)	B=+BMAX, RL=5k to GND EE_CL=enable		99		%VDD
Output Operating Range	VOOR	5 V linear operating range	0.5		4.5	V
		3.3 V linear operating range	0.3		3	V
Output Slew Rate	SR	Sen, CL	0.8	-	-	V/uS
Rise Time	tr	TA = 25°C, CL = 1 nF, 10%-90% of 1 V output swing		-		μS
VOUT Noise Peak-peak	Np-p	CLoad, Sen, TA, EENoise, EEBW	40	-	200	mVp-p
VOUT Noise RMS	NRMS	CLoad, Sen, TA, EENoise, EEBW	15	-	150	mVRMS
Chopping Frequency	Fc	-	-	2	-	MHz
Internal Bandwidth	BW	Signal -3dB, CL=1nF	120	400		KHZ
Refresh rate	Trr	guaranteed by design	0.8	1	2	uS
Magnetic Specifications						
Target Coarse VQ	VQT1	EE=0,B=0, Sen=-Smax--+Smax	-	50	-	%VDD
Target Coarse VQ	VQT2	EE=1,B=0, Sen=-Smax--+Smax	-	10	-	%VDD
Target Coarse VQ	VQT3	EE=2,B=0, Sen=-Smax--+Smax	-	0.5	-	V
Target Coarse VQ	VQT4	EE=3,B=0, Sen=-Smax--+Smax	-	0.33	-	V
Target Coarse VQ	VQT1	EE=4,B=0, Sen=-Smax--+Smax		1.35		V

Target Coarse VQ	VQT2	EE=5,B=0, Sen=-Smax--+Smax		1.5		V
Target Coarse VQ	VQT3	EE=6,B=0, Sen=-Smax--+Smax		1.65		V
Target Coarse VQ	VQT4	EE=7,B=0, Sen=-Smax--+Smax		2.5		V
VQ Programming Range	VQPR	B=0, Sen=Smax, EE=+-max	2.3	-	2.7	V
Bits for VQ Programming	VQBits	guaranteed by design	-	10	-	bit
Steps for VQ Programming	VQStep	Scan the EE for VQ	-	0.39	0.5	mV
VQ Accuracy After Programming	VQAcc	B=0, Sen=Smax, EE=+-max	-0.5	0	0.5	mV
VQ Drift though Temperature Range	VQTemp	TA=-40--150°C	-0.5	0	0.5	Gs
VQ Total Accuracy	ACCVQ		-5	0	5	mV
Linear Output Range	VOUMLN		10	-	90	%
Input Magnetic Range	BRG	guaranteed by design	±450	-	±4500	Gs
Sensitivity Mode with VDD	Msen	VDD=4.5--5.5V	-	-	-	%
Sensitivity Range	SRG	guaranteed by design	0.4	-	4	mV/Gs
Steps for Sen Programming	SStep	Scan the EE for Sen	-	0.1	-	%
Sen Accuracy After Programming	SAcc	Sen=Smax, EE=+-max	-1	0	1	%
Sen Drift though Temperature Range	STemp	TA=-40--150°C	-0.5	0	0.5	%
Sen Total Accuracy	ACCS		-1	0	1	%
Linearity Error	LN		-0.2	0	0.2	%
PSRR	PSRR1	0-1kHz, 100mV pk-pk ripple on VCC B=0	-	40	-	dB
PSRR	PSRR2	1k-100kHz, 100mV pk-pk ripple on VCC B=0	-	25	-	dB
Diagnostic Specifications						
DIAG_Level LOW	DIAGL		0	-	4	%VDD
DIAG_Level HIGH	DIAGH		96	-	100	%VDD
OCD Specifications (SIP4 with OCD)						
OCD Internal ON Resistance	RON_OCD	B=400,RL=5k to VDD	-	100	-	Ω
OCD Accuracy	ACCOCD	B=200G to 400G	-10	0	10	%Thr
OCD Response Time	tFR	B=200G to 400G,tr=10ns	-	1	2	us
OCD Release Time	tFC	B=400G to 200G,tf=10ns	-	1	2	us

OCD Input Holding Time	tOCD_Hold	guaranteed by design	-	0.5	-	us
OCD Output Dwell Time	tOCD_DW	B=400G to 200G,tf=10ns	-	10	-	us
OCD Programming Range	OCDRG		50	-	250	%FS
REF Specifications (SIP4 with REF)						
Target Coarse VREF	VREF1	EE=0,B=0, Sen=-Smax--+Smax	-	50	-	%VDD
Target Coarse VREF	VREF2	EE=1,B=0, Sen=-Smax--+Smax	-	10	-	%VDD
Target Coarse VREF	VREF3	EE=2,B=0, Sen=-Smax--+Smax	-	0.5	-	V
Target Coarse VREF	VREF4	EE=3,B=0, Sen=-Smax--+Smax	-	0.33	-	V
Target Coarse VREF	VREF5	EE=4,B=0, Sen=-Smax--+Smax		1.35		V
Target Coarse VREF	VREF6	EE=5,B=0, Sen=-Smax--+Smax		1.5		V
Target Coarse VREF	VREF7	EE=6,B=0, Sen=-Smax--+Smax		1.65		V
Target Coarse VREF	VREF8	EE=7,B=0, Sen=-Smax--+Smax		2.5		V
VREF Programming Range	VREFPR	EE=0, B=0, Sen=Smax, EE=+-max	2.4	-	2.6	V
Bits for VREF Programming	VREFBits	guaranteed by design	-	9	-	bit
Steps for VREF Programming	VREFStep	Scan the EE for VREF	-	0.39	0.5	mV
VREF Accuracy After Programming	VQAcc	B=0, Sen=Smax, EE=+-max	-0.5	0	0.5	mV
VREF Total Accuracy	ACCVREF		-5	0	5	mV

8 Detail Description

8.1 Overview

The SC4665 is a monolithic programmable Hall sensor, featuring <math><1\%</math> sensitivity drift across temperature, <math><0.5\%</math> full-scale linear error across temperature and device options providing both unidirectional and bidirectional magnetic field sensing. The SC4665 can measure magnetic field range up to 4500Gs and be applied from -40°C to 150°C. The magnetic field is sensed by a Hall sensor and is amplified by a precision signal chain. The SC4665 has a very fast response time (2 μs) and a bandwidth of 400kHz. The SC4665 can operate with a voltage supply from 4.5 V to 5.5 V. The SC4665 is optimized for high accuracy and temperature stability, with both offset and sensitivity compensated across the entire operating temperature range.

8.2 Functional Block Diagram

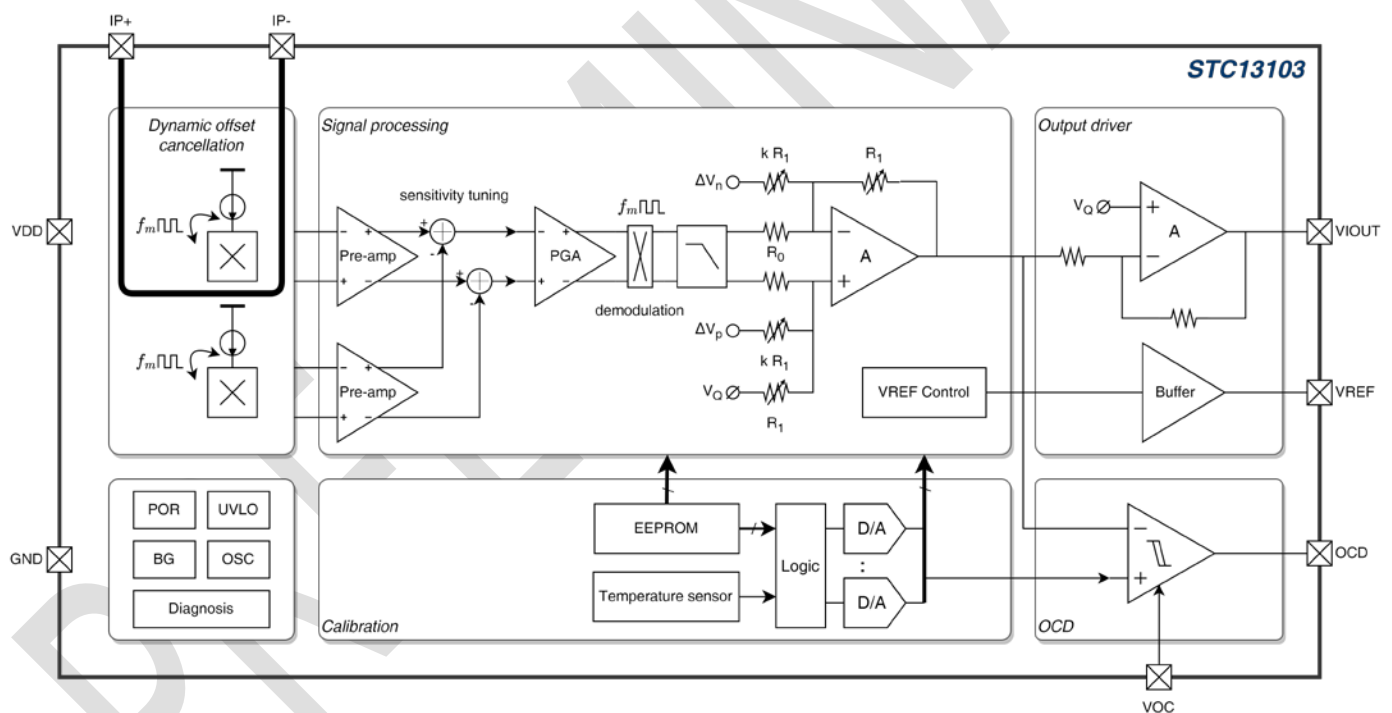


Figure 8-1. Functional Block Diagram

8.3 Feature Description

The descriptions in this section assume: $T_A = 25^{\circ}\text{C}$, no output load (R_L , C_L).

8.3.1 Power-On and Power-down

8.3.1.1 Power On

At power-up, as V_{CC} ramps up, the output is in a high-impedance state. When V_{CC} crosses V_{PORH} [1]/[1'], the POR Release counter starts counting for t_{PORR} . At this point, if V_{CC} exceeds V_{UVLOH} [2], the output will go to the default after t_{UVLOD} [3']. If V_{CC} does not exceed V_{UVLOH} [2], the output will stay in the high-impedance state until V_{CC} reaches V_{UVLOH} [3] and then go to setting output after t_{UVLOD} [4].

V_{CC} drops below $V_{CC(min)} = 4.5\text{ V}$. If V_{CC} drops below V_{UVLOL} [4']/[5], the UVLO Enable Counter starts counting. If V_{CC} is still below V_{UVLOL} when the counter reaches t_{UVLOE} , the UVLO function will be enabled and the output will be pulled near GND [6]. If V_{CC} exceeds V_{UVLOL} before the UVLO Enable Counter reaches t_{UVLOE} [5'], the output will continue to be the default.

Coming out of UVLO While UVLO is enabled [6], if V_{CC} exceeds V_{UVLOH} [7], UVLO will be disabled after t_{UVLOD} , and the output will be the default [8].

8.3.1.2 Power Down

As V_{CC} ramps down below V_{UVLOL} [6']/[9], the UVLO Enable Counter will start counting. If V_{CC} is higher than V_{PORL} when the counter reaches t_{UVLOE} , the UVLO function will be enabled and the output will be pulled near GND [10]. The output will enter a high-impedance state as V_{CC} goes below V_{PORL} [11]. If V_{CC} falls below V_{PORL} before the UVLO Enable Counter reaches t_{UVLOE} , the output will transition directly into a high-impedance state [7'].

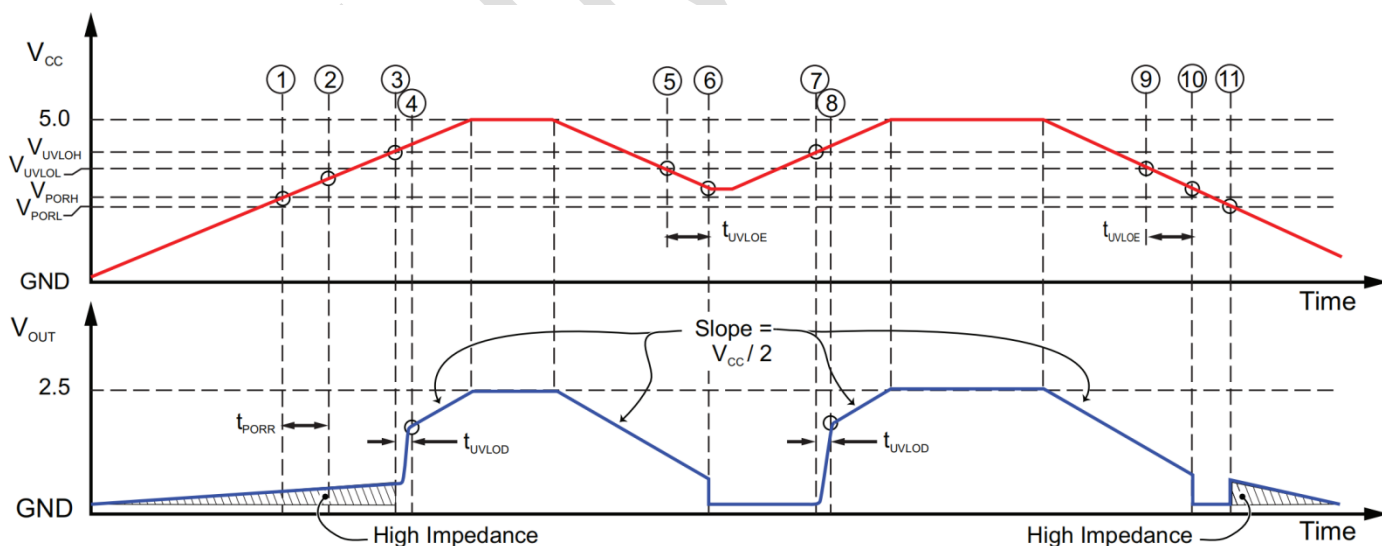


Figure 8-2. POR and UVLO Operation – Slow Rise Time Case

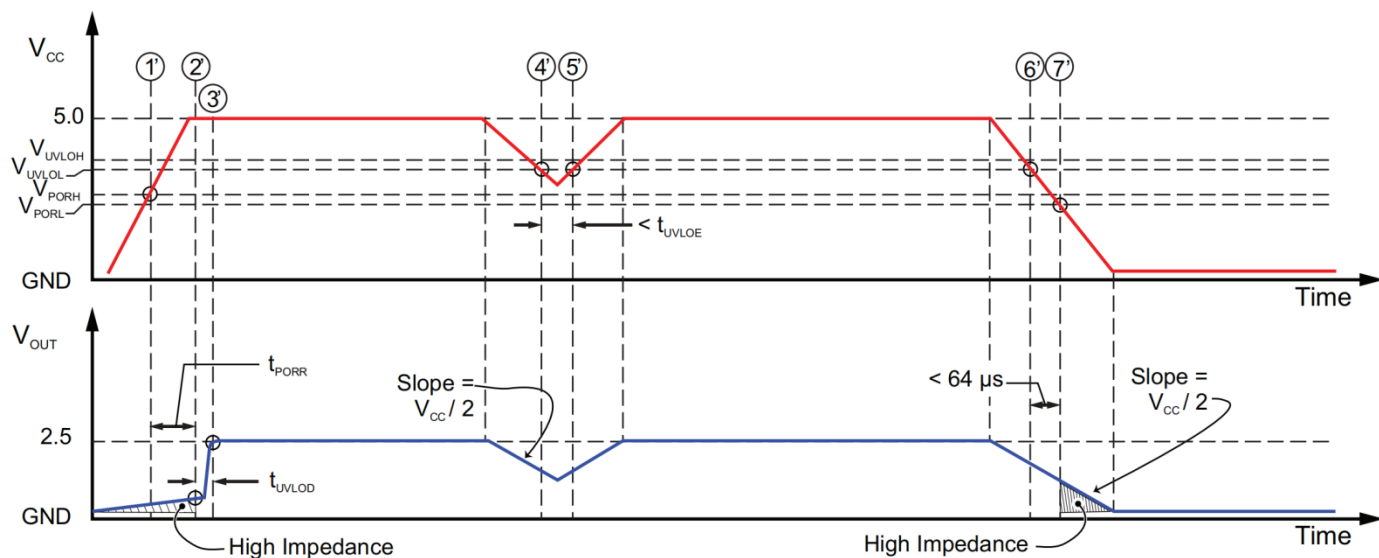


Figure 8-3. POR and UVLO Operation – Fast Rise Time Case

8.3.2 CLAMP

The SC4665 has a Clamp function used to limit the output voltage. When sensing a large magnetic field, the maximum output is limited at 95%VDD and the minimum output is limited at 5%VDD.

8.3.3 Over-Current Detection (OCD)

8.3.3.1 Fast Over-Current Detection (OCD)

The Over-Current Detection (OCD) function allows fast detection of over-current events. The raw analog output of the Hall probes is fed directly into comparators with programmable switching thresholds. A user programmable deglitch filter is implemented to enable the suppression of fast switching transients. The two different open-drain OCD pins are active low and can be directly combined into a wired-AND configuration on board level to have a general over-current detection signal.

The OCD pins are providing a very fast response, thanks to independence from the main signal path. They can be used as a trap functionality to quickly shut down the current source as well as for precise detection of soft overload conditions.

8.3.3.2 OCD pins external connection

The OCD pins can be connected to a logic input pin of the micro-controller and/or the gate-driver to quickly react to over-current events. They are designed as open-drain outputs to easily setup a wired-AND configuration and allow monitoring of several current sensors outputs via only one micro-controller pin.

8.3.3.3 OCD thresholds

The symmetric threshold level of the OCD outputs is adjustable and triggers an over-current event in case of a positive or negative over-current. The instruction for the settings is documented in the SC4665 programming guide and the SC4665 addendum.

8.3.4 OTP

The SC4665 has a over-temperature protection function. When temperature raising over the thresholds, the SC4665 will enter the fault mode and the performance of the output voltage is according to the setting of the F_OTP_MO in the EEPROM.

8.3.5 OVP

The SC4665 has a over-voltage protection function. When voltage of VDD raising over the thresholds, the SC4665 will enter the fault mode and the performance of the output voltage is according to the setting of the F_OV_MO in the EEPROM.

8.3.6 Low-pass filter

Low-pass filter allows signals with frequencies below a certain cutoff frequency to pass through while attenuating signals with frequencies above that cutoff. Low-pass filters help to ensure that only the desired frequency range of the signal is transmitted, reducing interference and improving overall signal quality. Overall, low-pass filters improve the overall performance and reliability of the system.

8.3.7 Fast response circuitry

Fast response circuitry is designed to react promptly to step signals. This ensures that critical transients or rapid changes in the system are captured and responded to in a timely manner, even if they fall outside the frequency range typically allowed by the filter.

8.3.8 temperature-coefficient

SC4665 use 16-segment temperature compensation algorithm. It improves the sensitivity drift and zero-point voltage drift at full temperature range. Each segment can adjust sensitivity and output voltage independently. The user can read the temperature through the temperature sensor. The temperature node of each segment can be freely set by the user.

8.4 EEPROM Programming Information

8.4.1 Programming Serial Interface

The SC4665 incorporates a serial interface that allows an external controller to read and write

registers in the EEPROM and volatile memory. Each transaction is initiated by a command from the controller; the SC4665 does not initiate any transactions. Three commands are recognized by the device: Write Access Code, Write, and Read. As shown in Figure 8-4, the SC4665 receives all commands via the OUT pin. It responds to Read commands via the VOUT pin. This implementation of Manchester encoding requires the communication pulses be within a high and low range of voltages for the VOUT line. The Write command to EEPROM is supported by two high voltage pulses on the VOUT line.

8.4.2 Writing The Access Code

In order for the external controller to write or read from the SC4665 memory during the current session, it must establish serial communication with the SC4665 by sending a Write command including the Access Code within Access Code Time Out from power-up.

8.4.3 Writing to Volatile Memory

In order for the external controller to write to volatile memory, a Write command must be transmitted on the VDD pin. Successive Write commands to volatile memory must be separated by t_{WRITE} .

8.4.4 Writing To EEPROM

In order for the external controller to write to non-volatile EEPROM, a Write command must be transmitted on the VDD pin. The controller must also send two Programming pulses, long high-voltage strobes via the VOUT pin. These strobes are detected internally, allowing the SC4665 to boost the voltage on the EEPROM gates.

8.4.5 Reading From EEPROM Or Volatile Memory

In order for the external controller to read from EEPROM or volatile memory, a Read command must be transmitted on the VDD line. Within time t_{start_read} , the VOUT line will stop responding to the magnetic field and the Read Acknowledge frame will be transmitted on the VOUT line. The Read Acknowledge frame contains Read data.

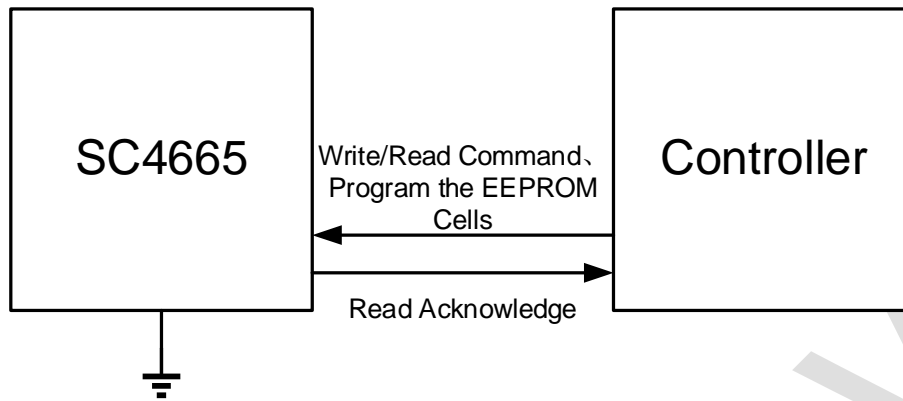


Figure 8-4. Programming Interface

8.4.6 Register map

The following Figure 8-5. and 8-6. shows the Register map of SC4665. Figure 8-5. shows the functions of the SC4665. SC4665 has a 16-segment temperature compensation algorithm. Each segment register map is as Figure 8-6. showed.

A[7:0]	Bit[7]	Bit[6]	Bit[5]	Bit[4]	Bit[3]	Bit[2]	Bit[1]	Bit[0]
0x00	ID_CUST[23:16]							
0x01	ID_CUST[15:8]							
0x02	ID_CUST[7:0]							
0x03	IK_CUST		UD_OUT	VQ			T_OCD_HLD	
0x04	OCD_TH		T_OCD_MSK		NO_OCD	NO_CLMP	USE_BK	
0x05	G1		G2		NO_NOTCH	NO_F_RSP	F_RSP_TH	
0x06	COMM_WIN		CL		MO_3V3	REF_IN	G_RT[9:8]	
0x07	0	ECC_0306						
0x08	G_RT[7:0]							
0x09	OTP_H[11:4]							
0x0A	OTP_H[3:0]				OTP_L[11:8]			
0x0B	OTP_L[7:0]							
0x0C	0	ECC_080B						
0x0D	F_OV_MO		F_OTP_MO		F_EE_MO		F_GAIN_MO	
0x0E	F_OCD_MO		F_HL_MO		F_TEMP_MO		F_UVLO_MO	
0x0F	0	0	0	0	0	0	0	0
0x10	CLMP_LVL	OW_OD	SWP_DIR_M	SWP_DIR_S	CL_MO	0	T_TRK	
0x11	0	ECC_0D10						
0x12	CAL_T[0]							
0x13								
0x14								
0x15								
0x16								
0x17								

Figure 8-5. Register map of function

A[7:0]	Bit[7]	Bit[6]	Bit[5]	Bit[4]	Bit[3]	Bit[2]	Bit[1]	Bit[0]
0xXX+0x00	TJ[11:4]							
0xXX+0x01	dVQ[9:2]							
0xXX+0x02	dS[9:2]							
0xXX+0x03	dVREF[8:1]							
0xXX+0x04	dVREF[0]	ECC_CAL[6:0]						
0xXX+0x05	TJ[3:0]				dVQ[1:0]		dS[1:0]	

Figure 8-6. Register map of each segment CAL_T

8.4.7 Induction Magnetic Field

UD_OUT locates at bit[5] in Address 0x03. It defines the unidirectional output of SC4665. By setting this bit, SC4665 will be affected only by unidirectional magnetic field. The default setting is 0.

SWP_DIR locates at bit[5] in Address 0x10. It defines the polarity of magnetic field that SC4665 induces. The default setting is 0.

8.4.8 Quiescent Voltage

VQ locates at bit[2] to bit[4] in Address 0x03. They define the output voltage without external magnetic field. It has four stages. When its code is 000 or 001, the output voltage is proportional to the VDD. Code for other than VQ, the output is a constant voltage. The default setting is 3b'000.

Table 8-1. VQ code

VQ	Code
0.5x VDD	000
0.1x VDD	001
0.5V	010
0.33V	011
1.35V	100
1.5V	101
1.65V	110
2.5V	111

8.4.9 OCD

T_OCD_HLD locates at bit[0] and bit[1] in Address 0x03. They define OCD duration time. When the OCD is triggered, the OCD alarm will hold at least a period of time according to the setting even if

OCD is clear. The default code is 00.

T_OCD_MSK locates at bit[3] and bit[4] in Address 0x04. They define OCD delay time. When the OCD is triggered, the OCD alarm will delay according to the setting even if OCD is clear. The default code is 00.

Table 8-2. Time of T_OCD_HLD and T_OCD_MSK code

OCD hold time	Code	OCD mask time	Code
0 us	00	0ns	00
10 us	01	250ns	01
2.05 us	10	500ns	10
5.12 us	11	750ns	11

OCD_TH bits locates at bit[5] to bit [7] in Address 0x04. They define OCD threshold. It stands for Over-current Detection Threshold and decide the limit of the strength of the magnetic field that OCD will take action to open alarm. The default code is 3b'000.

Table 8-3. OCD_TH code

OCD threshold	Code	OCD threshold	Code
300%FS	000	120%FS	100
250%FS	001	100%FS	101
200%FS	010	80%FS	110
150%FS	011	50%FS	111

NO_OCD locates at bit[2] in Address 0x04. By setting this bit, the OCD function will be closed and no longer respond to the over-current. The default setting is 0.

8.4.10 CLAMP

No_CLAMP locates at bit[1] in Address 0x04. By setting this bit, the CLAMP function will be closed. The default setting is 0.

8.4.11 GAIN

Gain bits define the multiplier of the SC4665 induced magnetic field. SC4665 has two Gain, GAIN 1 and GAIN 2. The total Gain equals to the product of GAIN 1 and GAIN 2.

GAIN 1 locates at bit[6] and bit[7] in Address 0x05 while **GAIN 2** locates at bit[4] and bit[5] in Address

0x05. The default setting of **GAIN 1** and **GAIN 2** are all 00.

Table 8-4. Multiplier of GAIN code

GAIN 1	Code	GAIN 2	Code
1x	00	1x	00
2x	01	2x	01
4x	10	4x	10
8x	11	8x	11

8.4.12 Low-pass Filter

NO_NOTCH locates at bit[3] in Address 0x05. By setting this bit, low-pass filter will be disabled. And it will enlarge high-frequency noise and shorten the response time of SC4665. The default setting is 0.

8.4.13 Fast Response Circuitry

NO_F_RSP locates at bit[2] in Address 0x05. By setting this bit, fast response circuitry will be disabled. Whether the step signal will be filtered by the low-pass filter depends on its frequency. The default setting is 0.

F_RSP_TH locates at bit[0] and bit[1] in Address 0x05. They define the threshold of fast response. The default setting is 0.

8.4.14 Communication Window

COMM_WIN locates at bit[6] and bit[7] in Address 0x06. They define the duration startup that enables to input protocol via OUT pin. If it is over time, SC4665 cannot be communicated. If it is set 11, the SC4665 will be locked and can never be communicated. The default setting of this code is 00.

Table 8-5. Duration Time of Communication Window

COMM_WIN	Code
100ms	00
50ms	01

20ms	10
0ms	11

8.4.15 Output

CL locates at bit[4] and bit [5] in Address 0x06. They define the external capacitor range that should be used. If external capacitor used is out of range, it will cause output shocking. The default code is 00.

Table 8-6. external capacitor range of CL code

OUT capacitor	Code
1nf - 4.7nf	00
	01
4.7nf - 10nf	10
	11

CL_MO locates at bit[3] in Address 0x10. It defines the function of OUT current limit mode. By setting this bit, the OUT current will be limited. The default setting is 0.

8.4.16 Sensitivity

G_RT is 10 bits, which define the GAIN of SC4665 at 25°C. It locates at Address 0x08 and bit[0] and bit[1] in Address 0x06. The $G_RT_{maxcode}$ is 511, and $G_RT_{mincode}$ is 512. The default setting of this code is 10h'000.

8.4.17 Over-temperature Protection

OTP_H is 12 bits, which locates at Address 0x09 and bit[4] to bit[7] in Address 0x0A. They define the trip point of over-temperature protection. The $OTP_H_{maxcode}$ is 2047, and $G_RT_{mincode}$ is 4095. The default setting of this code is 12h'000.

OTP_L is 12 bits, which locates at Address 0x0B and bit[0] to bit[3] in Address 0x0A. They define the recovery point of over-temperature protection. The $OTP_H_{maxcode}$ is 2047, and $G_RT_{mincode}$ is 4095. The default setting of this code is 12h'000.

8.4.18 Self-test Mode

SC4665 has many self-test modes that are listed as follows.

F_OV_MO locates at bit[6] and bit[7] in Address 0x0D, about fault mode of Over-voltage

protection.

F_OTP_MO locates at bit[4] and bit[5] in Address 0x0D, about fault mode of Over-temperature protection.

F_EE_MO locates at bit[2] and bit[3] in Address 0x0D, about fault mode of ECC.

F_GAIN_MO locates at bit[0] and bit[1] in Address 0x0D, about fault mode of Gain stage self-test.

F_OCD_MO locates at bit[6] and bit[7] in Address 0x0E, about fault mode of Over-current detection.

F_HL_MO locates at bit[4] and bit[5] in Address 0x0E, about fault mode of Hall bias self-test.

F_TEMP_MO locates at bit[2] and bit[3] in Address 0x0E, about fault mode of Temperature sensor self-test failure.

F_UVLO_MO locates at bit[0] and bit[1] in Address 0x0E, about fault mode of UVLO.

By setting each of these fault modes to 00, it will disable this function. The other settings are listed in TABLE. The default code is 00.

Table 8-7. Fault mode of self-test

Default mode	Code
Disabled	00
HZ	01
Pull OUT L	10
Pull OUT H	11

8.4.19 OW_OD

OW_OD locates at bit[6] in Address 0x10. It defines the function of one-wire open-drain output. By setting this bit, the OUT current will be open. The default setting of this code is 0.

8.4.20 CAL_T[15:0]

CAL_T includes temperature of segment point, temperature-coefficient effects of VQ & GAIN calibration.

T_J is used to locate the temperature, while the value of **T_J** is according to the temperature sensor.

dVQ has 10 bits used to calibrate. **VQ_{maxcode}** is 511, and **VQ_{mincode}** is 512.

dS has 10 bits used to calibrate. **GAIN_{maxcode}** is 511, and **GAIN_{mincode}** is 512.

8.4.21 ECC

ECC is used to correct the single bit or detect the fault of double bits error in the EEPROM. SC4665 has three ECC for Address 0x03-0x06, Address 0x08-0x0B and Address 0x0D-0x10. Furthermore, Each segment of temperature coefficient has one ECC.

9 Characteristic Definitions

9.1 Power-On Time (t_{PO})

When the supply is ramped to its operating voltage, the device requires a finite time to power its internal components before responding to an input magnetic field.

Power-On Time (t_{PO}) is defined as: the time it takes for the out- put voltage to settle within $\pm 10\%$ of its steady-state value under an applied magnetic field, after the power supply has reached its minimum specified operating voltage ($V_{CC(min)}$) as shown in Figure 9-1.

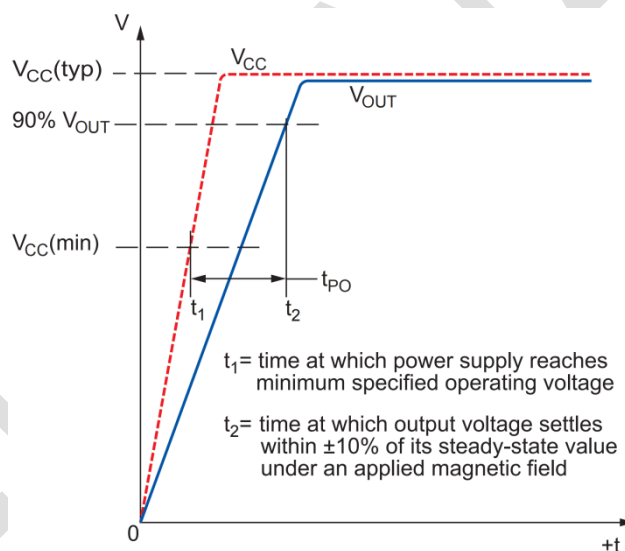


Figure 9-1. Power-On Time Definition

9.2 Temperature Compensation Power-On Time (t_{TC})

After Power-On Time (t_{PO}) elapses, t_{TC} is also required before a valid temperature compensated output.

9.3 Propagation Delay (t_{pd})

The time interval between a) when the applied magnetic field reaches 20% of its final value, and b) when the output reaches 20% of its final value (see Figure 6).

9.4 Rise Time (t_r)

The time interval between a) when the sensor IC reaches 10% of its final value, and b) when it reaches 90% of its final value (see Figure 9-2). Both t_r and t_{RESPONSE} are detrimentally affected by eddy current losses observed in the conductive IC ground plane.

9.5 Response Time (t_{RESPONSE})

The time interval between a) when the applied magnetic field reaches 80% of its final value, and b) when the sensor reaches 80% of its output corresponding to the applied magnetic field (see Figure 9-3).

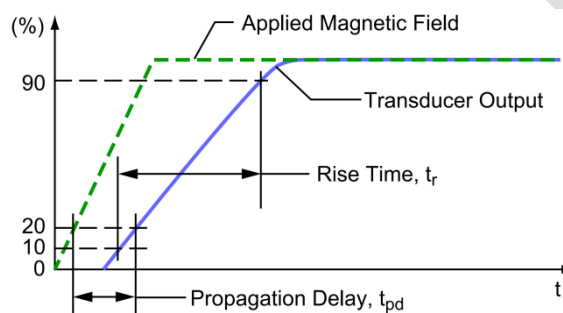


Figure 9-2. Propagation Delay and Rise Time Definitions

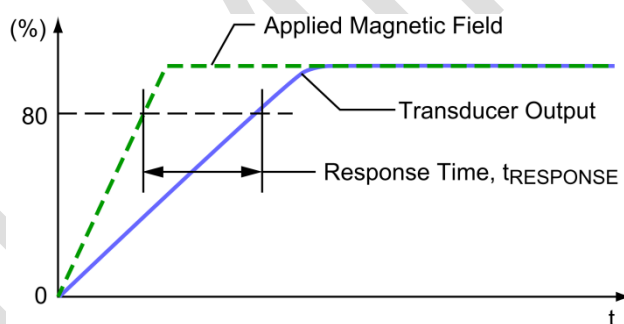


Figure 9-3. Response Time Definition

9.6 Delay to Clamp (t_{CLP})

A large magnetic input step may cause the clamp to overshoot its steady-state value. The Delay to Clamp (t_{CLP}) is defined as: the time it takes for the output voltage to settle within steady-state clamp voltage $\pm 1\%$ of Clamp Voltage Dynamic Range, after initially passing through its steady-state voltage, as shown in Figure 9-4. Clamp Voltage Dynamic Range is defined as $V_{\text{CLP(HIGH)min}} - V_{\text{CLP(LOW)max}}$.

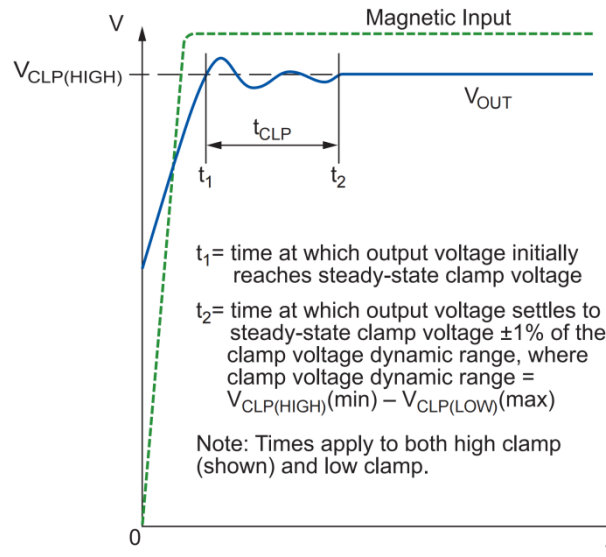


Figure 9-4. Delay to Clamp Definition

9.7 Quiescent Voltage Output ($V_{OUT(Q)}$)

In the quiescent state (no significant magnetic field: $B = 0$ G), the output ($V_{OUT(Q)}$) is a constant voltage or has a constant ratio to the supply voltage (V_{CC}) throughout the entire operating ranges of V_{CC} and ambient temperature (T_A).

9.8 Initial Unprogrammed Quiescent Voltage Output ($V_{OUT(Q)init}$)

Before any programming, the Quiescent Voltage Output ($V_{OUT(Q)}$) has a nominal value of $V_{CC} / 2$.

9.9 Quiescent Voltage Output Temperature Coefficient (TC_{QVO})

Device $V_{OUT(Q)}$ changes as temperature changes, with respect to its programmed Quiescent Voltage Output Temperature Coefficient, TC_{QVO} . TC_{QVO} is programmed at 150°C and is calculated relative to the nominal $V_{OUT(Q)}$ programming temperature of 25°C . TC_{QVO} ($\text{mV}/^\circ\text{C}$) is defined as:

$$TC_{QVO} = \frac{[V_{OUT(Q)T2} - V_{OUT(Q)T1}]}{T2 - T1} \quad (1)$$

where $T1$ is the nominal $V_{OUT(Q)}$ programming temperature of 25°C , and $T2$ is the TC_{QVO} programming temperature of 150°C . The expected $V_{OUT(Q)}$ through the full ambient temperature range ($V_{OUT(Q)EXPECTED(TA)}$) is defined as:

$$V_{OUT(Q)EXPECTED(TA)} = V_{OUT(Q)T1} + TC_{QVO}(T_A - T_1) \quad (2)$$

$V_{OUT(Q)EXPECTED(TA)}$ should be calculated using the actual measured values of $V_{OUT(Q)T1}$ and TC_{QVO} rather than programming target values.

9.10 Quiescent Voltage Output Drift Through Temperature Range ($V_{OUT(Q)TC}$)

Due to internal component tolerances and thermal considerations, the Quiescent Voltage Output ($V_{OUT(Q)}$) may drift from its nominal value through the operating ambient temperature (T_A). The Quiescent Voltage Output Drift Through Temperature Range ($V_{OUT(Q)TC}$) is defined as:

$$D_{V_{OUT(Q)TC}} = V_{OUT(Q)(T_A)} - V_{OUT(Q)EXPECTED(T_A)} \quad (3)$$

$\Delta V_{OUT(Q)TC}$ should be calculated using the actual measured values of $\Delta V_{OUT(Q)(T_A)}$ and $\Delta V_{OUT(Q)EXPECTED(T_A)}$ rather than programming target values.

9.11 Sensitivity (Sens)

The presence of a south polarity magnetic field, perpendicular to the branded surface of the package face, increases the output voltage from its quiescent value toward the supply voltage rail. The amount of the output voltage increase is proportional to the magnitude of the magnetic field applied.

Conversely, the application of a north polarity field decreases the output voltage from its quiescent value. This proportionality is specified as the magnetic sensitivity, Sens (mV/G), of the device, and it is defined as:

$$\text{Sens} = \frac{V_{OUT(B_{POS})} - V_{OUT(B_{NEG})}}{B_{POS} - B_{NEG}} \quad (4)$$

where BPOS and BNEG are two magnetic fields with opposite polarities.

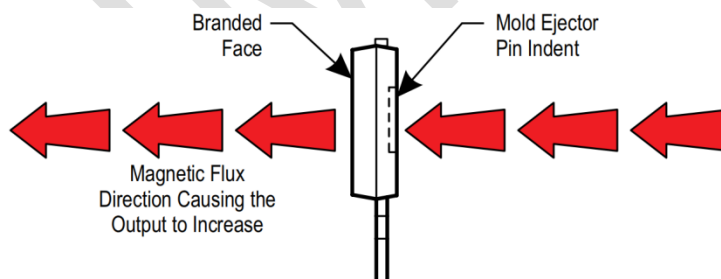


Figure 9-5. Magnetic Flux Polarity

9.12 Initial Unprogrammed Sensitivity ($Sens_{init}$)

Before any programming, Sensitivity has a nominal value that depends on the GAIN_STAGE_COARSE bits and G_RT bits setting.

9.13 Sensitivity Programming Range ($Sens_{PR}$)

The magnetic sensitivity (Sens) can be programmed around its initial value within the sensitivity range limits: $Sens_{PR(min)}$ and $Sens_{PR(max)}$. Exceeding the specified Sensitivity Range will cause Sensitivity Drift Through Temperature Range $Sens_{TC}$ to deteriorate beyond the specified values.

9.14 Average Fine Sensitivity Programming Step Size (Step_{SENS})

The Average Quiescent Voltage Output Programming Step Size (Step_{SENS}) is determined using the following calculation:

$$\text{Step}_{\text{SENS}} = \frac{\text{Sens}_{\text{maxcode}} - \text{Sens}_{\text{mincode}}}{2^n - 1} \quad (5)$$

where n is the number of available programming bits in the trim range, 10 bits, Sens_{maxcode} is at decimal code 511, and Sens_{mincode} is at decimal code 512.

9.15 Sensitivity Temperature Coefficient (TC_{SENS})

Device sensitivity changes as temperature changes, with respect to its programmed sensitivity temperature coefficient, TC_{SENS}. TC_{SENS} is programmed at 150°C, and calculated relative to the nominal sensitivity programming temperature of 25°C. TC_{SENS} (%/°C) is defined as:

$$\text{TC}_{\text{SENS}} = \frac{\text{Sens}_{T_2} - \text{Sens}_{T_1}}{\text{Sens}_{T_1} \times (T_2 - T_1)} \times 100\% \quad (6)$$

where T1 is the nominal Sens programming temperature of 25°C, and T2 is the TC_{SENS} programming temperature of 150°C. The expected value of Sens over the full ambient temperature range, Sens_{EXPECTED(TA)}, is defined as:

$$\text{Sens}_{\text{EXPECTED}(T_A)} = \text{Sens}_{T_1} \times \left[100\% + \frac{\text{TC}_{\text{SENS}}(T_A - T_1)}{100} \right] \quad (7)$$

Sens_{EXPECTED(TA)} should be calculated using the actual measured values of Sens_{T1} rather than programming target values.

9.16 Sensitivity Drift Through Temperature Range (Sens_{TC})

Temperature-coefficient effects cause the magnetic sensitivity, Sens, to drift from its expected value over the operating ambient temperature range (TA). The Sensitivity Drift Through Temperature Range (ΔSens_{TC}) is defined as:

$$\Delta \text{Sens}_{\text{TC}} = \frac{\text{Sens}_{T_A} - \text{Sens}_{\text{EXPECTED}(T_A)}}{\text{Sens}_{\text{EXPECTED}(T_A)}} \times 100\% \quad (8)$$

9.17 Sensitivity Drift Due to Package Hysteresis (Sens_{PKG})

Package stress and relaxation can cause the device sensitivity at TA = 25°C to change during and after temperature cycling. The sensitivity drift due to package hysteresis (ΔSens_{PKG}) is defined as:

$$\Delta \text{Sens}_{\text{PKG}} = \frac{\text{Sens}_{(25^\circ\text{C})2} - \text{Sens}_{(25^\circ\text{C})1}}{\text{Sens}_{(25^\circ\text{C})1}} \times 100\% \quad (9)$$

where Sens(25°C)1 is the programmed value of sensitivity at TA = 25°C, and Sens(25°C)2 is the value of sensitivity at TA = 25°C, after temperature cycling TA up to 150°C and back to 25°C.

9.18 Linearity Sensitivity Error (Lin_{ERR})

The SC4665 is designed to provide a linear output in response to a ramping applied magnetic field. Consider two magnetic fields, B1 and B2. Ideally, the sensitivity of a device is the same for both fields, for a given supply voltage and temperature. Linearity error is present when there is a difference between the sensitivities measured at B1 and B2.

9.19 Linearity Error

Linearity error is calculated separately for the positive (Lin_{ERRPOS}) and negative (Lin_{ERRNEG}) applied magnetic fields. Linearity Error (%) is measured and defined as:

$$\text{Lin}_{ERRPOS} = \left(1 - \frac{\text{Sens}_{B_{POS2}}}{\text{Sens}_{B_{POS1}}}\right) \times 100\% \quad (10)$$

$$\text{Lin}_{ERRNEG} = \left(1 - \frac{\text{Sens}_{B_{NEG2}}}{\text{Sens}_{B_{NEG1}}}\right) \times 100\% \quad (11)$$

where:

$$\text{Sens}_{B_x} = \frac{|V_{OUT(B_x)} - V_{OUT(Q)}|}{B_x} \quad (12)$$

and B_{POSx} and B_{NEGx} are positive and negative magnetic fields, with respect to the quiescent voltage output such that |B_{POS2}| = 2 × |B_{POS1}| and |B_{NEG2}| = 2 × |B_{NEG1}|.

Then:

$$\text{Lin}_{ERR} = \max(\text{Lin}_{ERRPOS}, \text{Lin}_{ERRNEG}) \quad (13)$$

9.20 Symmetry Sensitivity Error (Sym_{ERR})

The magnetic sensitivity of an SC4665 device is constant for any two applied magnetic fields of equal magnitude and opposite polarities. Symmetry Error, Sym_{ERR} (%), is measured and defined as:

$$\text{Sym}_{ERR} = \left(1 - \frac{\text{Sens}_{B_{POS}}}{\text{Sens}_{B_{NEG}}}\right) \times 100\% \quad (14)$$

where Sens_{Bx} is as defined in equation 12, and B_{POSx} and B_{NEGx} are positive and negative magnetic fields such that |B_{POSx}| = |B_{NEGx}|.

9.21 Ratiometry Error (Rat_{ERR})

The SC4665 device features ratiometric output. This means that the Quiescent Voltage Output (V_{OUT(Q)}) magnetic sensitivity, Sens, and Output Voltage Clamp (V_{CPL(HIGH)} and V_{CPL(LOW)}) are proportional to the Supply Voltage (V_{CC}). In other words, when the supply voltage increases or decreases by a certain percentage, each characteristic also increases or decreases by the same percentage. Error is the difference between the measured change in the supply voltage relative to 5 V, and the measured change in each characteristic.

The ratiometric error in Quiescent Voltage Output, $Rat_{ERRV_{OUT(Q)}} (%)$, for a given supply voltage (VCC) is defined as:

$$Rat_{ERRV_{OUT(Q)}} = \left(1 - \frac{V_{OUT(Q)(VCC)}/V_{OUT(Q)(5V)}}{V_{CC}/5V}\right) \times 100\% \quad (15)$$

The ratiometric error in magnetic sensitivity, $Rat_{ERRSens} (%)$, for a given Supply Voltage (VCC) is defined as:

$$Rat_{ERRSens} = \left(1 - \frac{Sens_{(VCC)}/Sens_{(5V)}}{V_{CC}/5V}\right) \times 100\% \quad (16)$$

The ratiometric error in the clamp voltages, $Rat_{ERRCLP} (%)$, for a given supply voltage (VCC) is defined as:

$$Rat_{ERRCLP} = \left(1 - \frac{V_{CLP(VCC)}/V_{CLP(5V)}}{V_{CC}/5V}\right) \times 100\% \quad (17)$$

where VCLP is either VCLP(HIGH) or VCLP(LOW).

9.22 Power-On Reset Voltage (V_{POR})

On power-up, to initialize to a known state and avoid current spikes, the SC4665 is held in Reset state. The Reset signal is disabled when VCC reaches V_{UVLOH} and time t_{PORR} has elapsed, allowing the output voltage to go from a high-impedance state into normal operation. During power-down, the Reset signal is enabled when VCC reaches V_{PORL} , causing the output voltage to go into a high-impedance state. (Note that a detailed description of POR and UVLO operation can be found in the Functional Description section).

9.23 Power-On Reset Release Time (t_{PORR})

When VCC rises to V_{PORH} , the Power-On Reset Counter starts. The SC4665 output voltage will transition from a high-impedance state to normal operation only when the Power-On Reset Counter has reached t_{PORR} and VCC has exceeded V_{UVLOH} . Under-voltage Lockout Threshold (V_{UVLO}) If VCC drops below V_{UVLOL} , the output voltage will be pulled to GND. If VCC starts rising, the SC4665 will come out of this lock state when VCC reaches V_{UVLOH} .

9.24 UVLO Enable/Disable Delay Time (t_{UVLO})

When a falling VCC reaches V_{UVLOL} , time t_{UVLOE} is required to engage the Undervoltage Lockout state. When VCC rises above V_{UVLOH} , time t_{UVLOD} is required to disable UVLO and to have a valid output voltage.

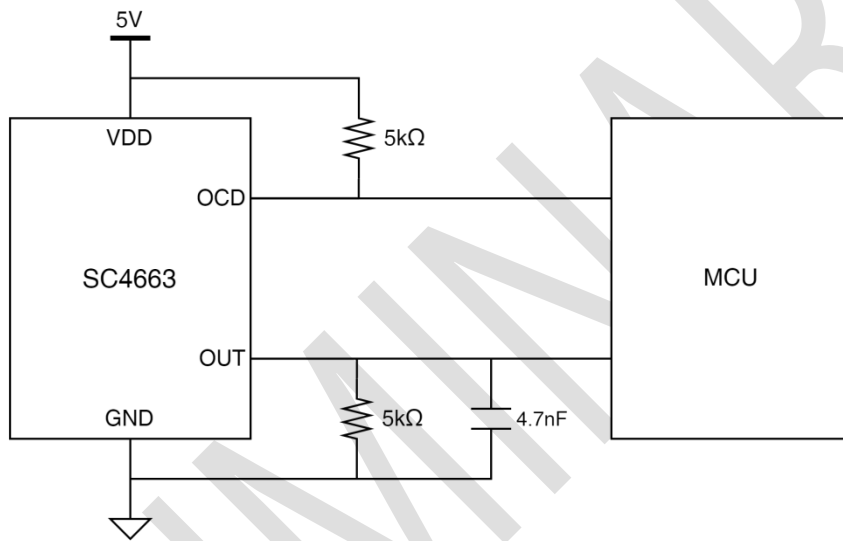
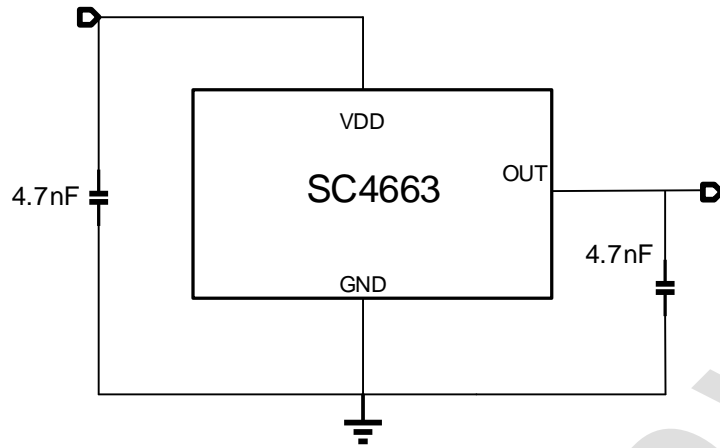
9.25 Output Saturation Voltage (V_{SAT})

When output voltage clamps are disabled, the output voltage can swing to a maximum of $V_{SAT(HIGH)}$ and to a minimum of $V_{SAT(LOW)}$.

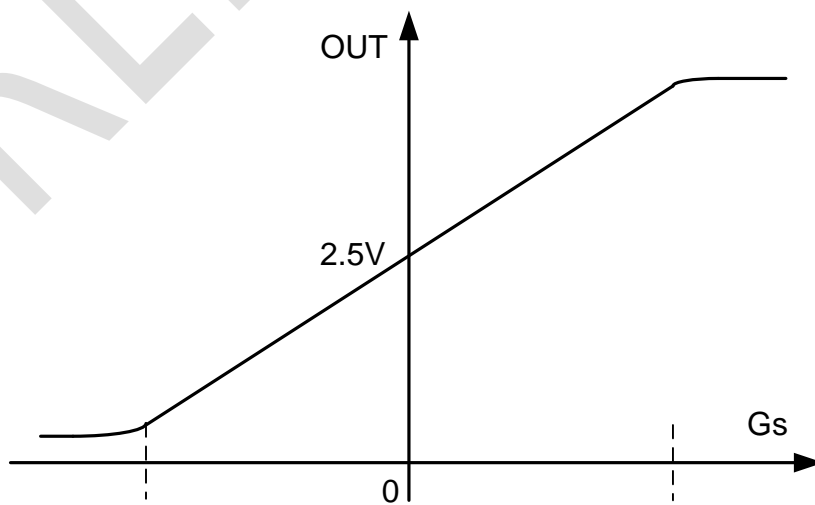
9.26 Broken Wire Voltage (V_{BRK})

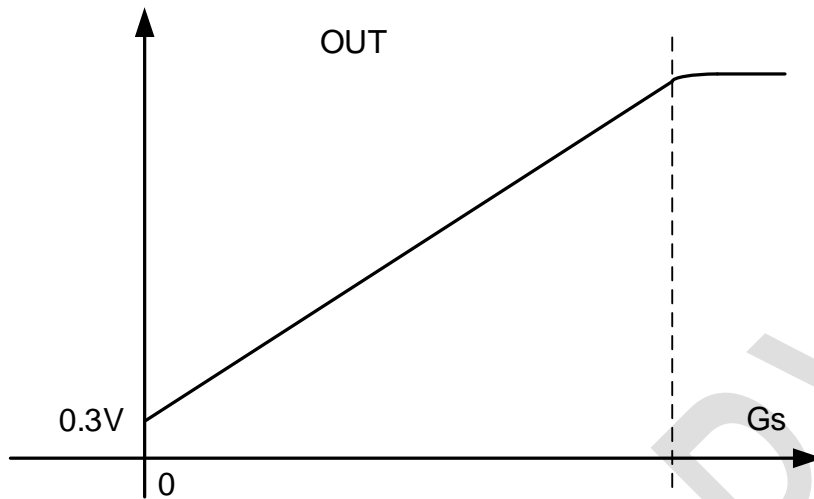
If the GND pin is disconnected (broken wire event), output voltage will go to $V_{BRK(HIGH)}$ if a load resistor is connected to VCC, or to $V_{BRK(LOW)}$ if a load resistor is connected to GND.

10 Typical Application Diagram



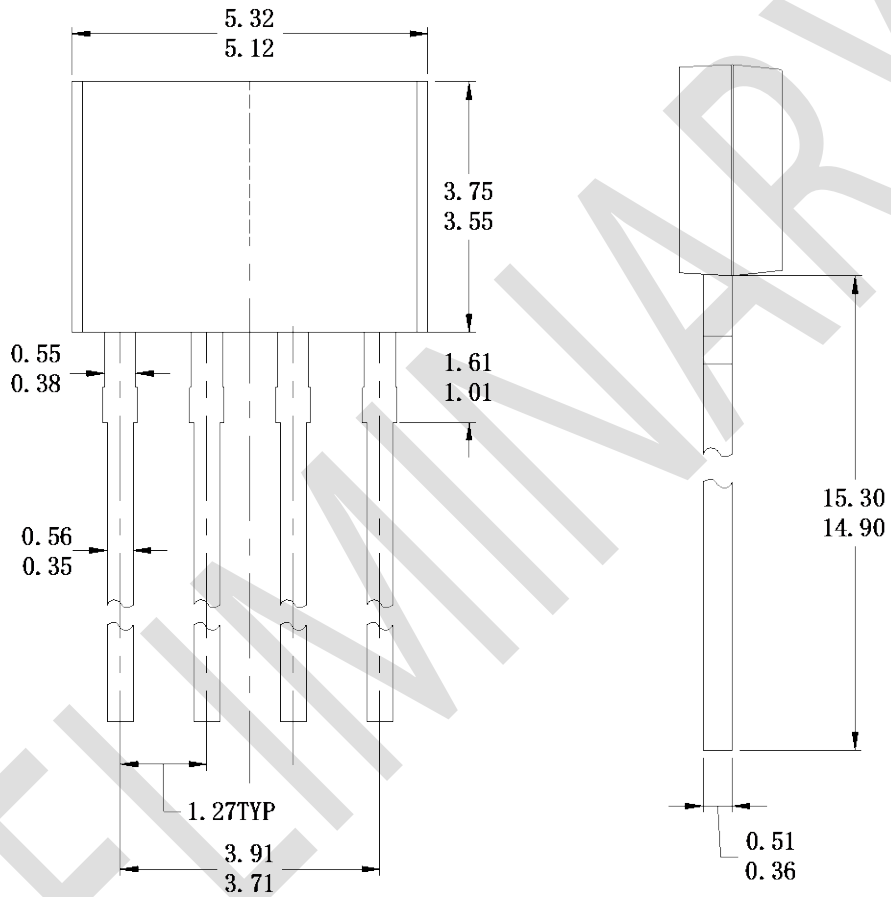
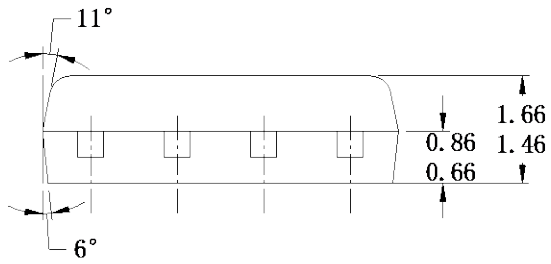
11 Transfer Function





12 Package Designator

12.1 Package(SIP4-VB)



12.2 Package(SIP3-VB)

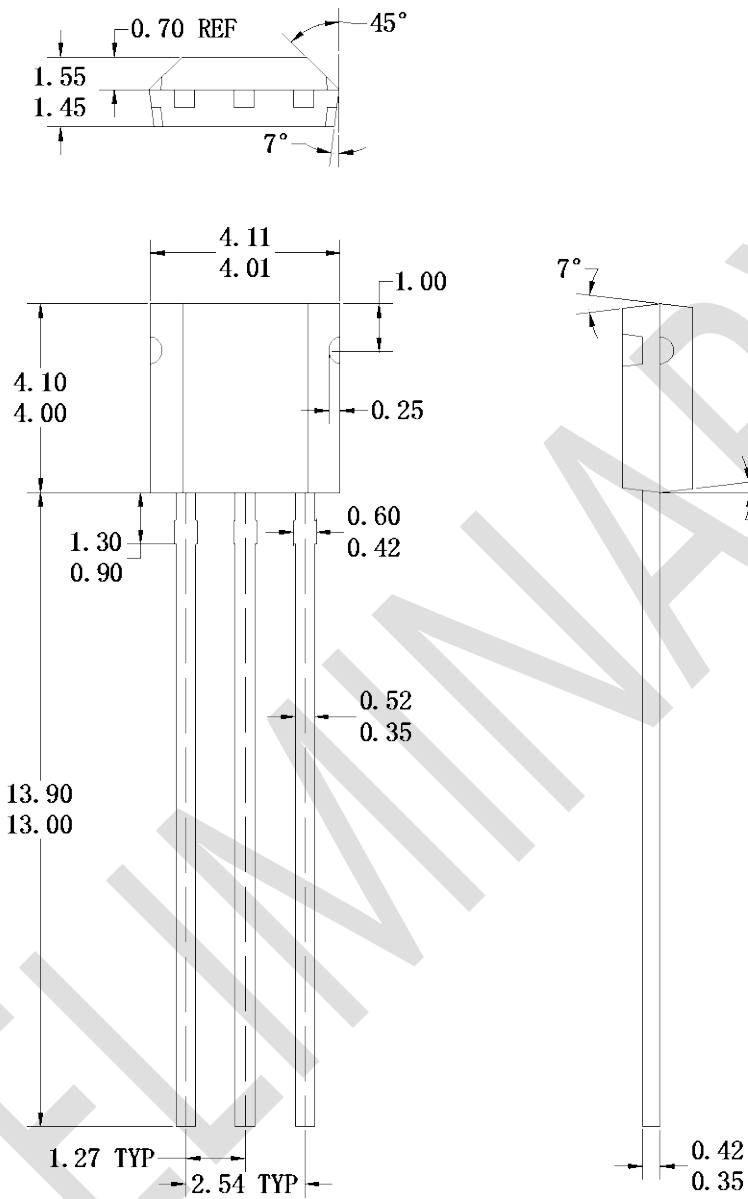


Figure: TO-92S-U Package Shape and Dimension in millimeters

- Notes:
- A. All linear dimensions are in millimeters.
 - B. Body dimension do not include mold flash
 - C. This package complies to JEDEC MS-012 variation BA

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